

AMENDMENTS TO THE CLAIMS

1. **(Currently amended)** A resin for a photoresist composition, having a first structural unit that comprises a hydroxyl group bonded to a carbon atom, wherein the first structural unit comprises comprising a -CR¹R²OH group only at a terminal of a principal chain of the resin, wherein R¹ and R² each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R¹ and R² is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups, wherein said -CR¹R²OH group is bonded at a principal chain terminal of a polymer of said resin.
2. **(Canceled).**
3. **(Original)** A resin for a photoresist composition according to claim 1, wherein said electron attractive group is a fluorine atom or a fluorinated alkyl group.
4. **(Previously presented)** A resin for a photoresist composition according to claim 1, wherein a proportion of the first structural unit comprising said -CR¹R²OH group is at least 1 mol%, relative to a combined 100 mol% of all structural units other than said first structural unit within said resin for a photoresist composition.
5. **(Canceled)**
6. **(Canceled)**
7. **(Previously presented)** A resin for a photoresist composition according to claim 1, further comprising an acid dissociable, dissolution inhibiting group.
8. **(Original)** A resin for a photoresist composition according to claim 7, further comprising (a1) a structural unit derived from a (meth)acrylate ester having an acid dissociable, dissolution inhibiting group, and (a2) a structural unit derived from a (meth)acrylate ester having a lactone ring.

9. **(Original)** A resin for a photoresist composition according to claim 8, further comprising
(a3) a structural unit derived from a (meth)acrylate ester having a hydroxyl group.

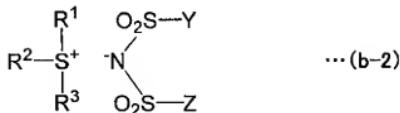
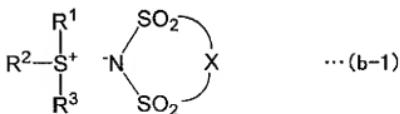
10. **(Previously presented)** A resin for a photoresist composition according to claim 1, with
a weight average molecular weight of no more than 12,000.

11. **(Previously presented)** A photoresist composition, comprising a resin for a photoresist
composition according to claim 1.

12. **(Original)** A photoresist composition according to claim 11, further comprising an acid
generator as a component (B).

13. **(Original)** A photoresist composition according to claim 12, comprising as said
component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.

14. **(Original)** A photoresist composition according to claim 12, comprising as said
component (B), a sulfonium compound represented by either of general formulas (b-1) and (b-2)
shown below:



wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represent, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen atom has been substituted with a

fluorine atom; R¹ to R³ each represent, independently, an aryl group or an alkyl group, and at least one of R¹ to R³ is an aryl group.

15. **(Original)** A photoresist composition according to claim 14, further comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.

16. **(Original)** A photoresist composition according to claim 11, further comprising a nitrogen-containing organic compound.

17. **(Previously presented)** A method for forming a resist pattern, using a photoresist composition according to claim 11, comprising the steps of:

- applying the photoresist composition to a surface of a substrate;
- performing selective exposure through a desired mask pattern; and
- performing developing to form a resist pattern.

18. **(Previously presented)** A resin for a photoresist composition according to claim 1, wherein a proportion of the first structural units constituting said resin is 1-5 mol%, relative to a combined 100 mol% of all structural units other than said first structural units within said resin.

19. **(Previously presented)** A resin for a photoresist composition according to claim 1, wherein the first structural unit which includes the carbon atom in the α -position of said hydroxyl group having at least one electron attractive group is substantively bonded only to the polymer terminal.

20. **(Previously presented)** A resin for a photoresist composition according to claim 5, wherein a proportion of the first structural units which have the substituents with a pKa value between 6 and 12 constituting said resin is 1-5 mol% relative to a combined 100 mol% of all structural units other than said first structural units within said resin.

21. **(Previously presented)** A resin for a photoresist composition according to claim 5, wherein the substituents with a pKa value between 6 and 12 are substantively bonded only to the polymer terminal.
22. **(New)** The resin for a photoresist composition according to claim 1, wherein a -S- $(CH_2)_m-C(CF_3)_2-OH$ group is introduced at a terminal of a principal chain of the resin, wherein m represents an integer from 2 to 4.
23. **(New)** A resin for a photoresist composition, comprising: a -CR¹R²OH group which is introduced at a terminal of a principal chain of the resin; and a structural unit derived from a (meth)acrylate ester containing an acid dissociable, dissolution inhibiting group, wherein R¹ and R² each represent, independently, an alkyl group, a halogen atom, or a halogenated alkyl group, and at least one of R¹ and R² is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups.
24. **(New)** The resin for a photoresist composition according to claim 23, wherein a -S- $(CH_2)_m-C(CF_3)_2-OH$ group is introduced at a terminal of a principal chain of the resin, wherein m represents an integer from 2 to 4.